

AMENDMENTS TO THE CLAIMS

1. - 4. (Cancelled).

5. - 9. (Cancelled).

10. (Original) A method of forming holes, comprising the steps of:
providing a substrate having a dielectric layer thereon;
forming a first resist layer having substantially parallel first trench patterns on the dielectric layer;
curing the first resist layer so that the first resist layer does not dissolve in a resist solvent;
forming a second resist layer having substantially parallel second trench patterns on the cured first resist layer, wherein the second trench patterns are substantially perpendicular to the first trench patterns; and
removing the dielectric layer under the intersections of the second trench patterns and the first trench patterns to form at least one hole.

11. (Original) The method as claimed in claim 10, wherein the step of curing the first resist layer is performed by ion implantation of argon or nitrogen into the first resist layer.

12. (Original) The method as claimed in claim 11, wherein the ion implantation is performed using an energy of 10 to 50 keV and a dose of 10^{13} to 10^{15} ions/cm².

13. (Original) The method as claimed in claim 10, wherein the step of curing the first resist layer is performed using argon plasma.

14. (Original) The method as claimed in claim 10, wherein the dielectric layer is mainly silicon dioxide.

15. - 20. (Cancelled).